



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 1765
Confirmation No.: 8712
Examiner: Not yet assigned

In Re PATENT APPLICATION OF

Applicant(s): Erik JANZÉN *et al.*

Appl'n No.: 10/830,047

Filing Date: April 23, 2004

For: DEVICE AND METHOD FOR
PRODUCING SINGLE CRYSTALS BY
VAPOR DEPOSITION

Att'y Dkt.: 35947-202834

INFORMATION DISCLOSURE STATEMENT

26694
U.S. PATENT AND
TRADEMARK OFFICE

September 10, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is an Information Disclosure Statement submitted under 37 C.F.R. § 1.97 within the time specified under 37 C.F.R. § 1.97(b).

Enclosed is a PTO-1449 and copies of references cited therein. The relevance of the non-English references is as follows. The article by Lely is discussed in the specification. Also, European patent 0 787 822 is discussed in the specification, an English abstract translation of the abstract is provided and U.S. patent 6,299,683 corresponds thereto.

Applicants respectfully request the Examiner to consider the cited publications and make them of record.

Respectfully submitted,

Date: 9/10/04

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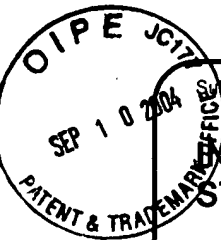
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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known

Application Number	0/830,047
Filing Date	April 23, 2004
First Named Inventor	Erik JANZEN et al.
Group Art Unit	1765
Examiner Name	tba
Attorney Docket Number	35947-202834

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	1	5,704,985	A	KORDINA et al.	01/06/1998	
	2	5,851,589	A	NAKAYAMA et al.	12/22/1998	
	3	5,985,024	A	BALAKRISHNA et al.	11/16/1999	
	4	6,039,812	A	ELLISON et al.	03/21/2000	
	5	6,048,398	A	VEHANEN et al.	04/11/2000	
	7	6,281,098	B1	WANG et al.	08/28/2001	
	8	2002/0056411	A1	HARA et al.	05/16/2002	
	9	6,299,683	B	Rupp et al.	10/09/2001	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₈
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
	10	WO	98/14644	A1		04/09/1998		
	11	EP	0554047	B1		11/29/1995		
	12	EP	0787822	B1		03/28/2001		
	13	GB	1231993			05/12/1971		
	14	GB	2218567	A		11/15/1989		
	15	JP	63033568	A		02/13/1988		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	16	VON J.A. LELY; Darstellung von Einkristallen von Siliciumcarbid und Beherrschung von Art and Menge der eingebauten Verunreinigungen; Berichte der Deutschen Keramischen Gesellschaft e.V.; August, 1955; Pages 229-231.	
	17	YU M. TAIROV and V.F. TSVETKOV; General Principles of Growing Large-Size Single Crystals of Various Silicon Carbide Polytypes; Journal of Crystal Growth 52 (1981) 146-150; pages 146-150; North-Holland Publishing Company.	
	18	J. ZHANG, O. KORDINA, A. ELLISON and E. JANZEN; In Situ Etching of 4H-SiC in H ₂ with Additional of HCl for Epitaxial CVD Growth; Materials Science Forum Vols. 389-393 (2002); pages 239-242; 2002 Trans Tech Publications, Switzerland	

Examiner Signature	Date Considered
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

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